

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2171	(insulated adj gate adj field adj effect adj transistor)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 11:10
L4	111	steven with peake	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 11:11
L5	3796	438/173,192,197,206,207,212.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/11 11:12
L6	2454	5 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2010/01/11 11:12
L7	96	6 and (insulated adj gate adj field adj effect adj transistor)	US-PGPUB; USPAT	OR	ON	2010/01/11 11:12
L8	3550	257/330,220,262,350.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/11 11:16
L9	2556	8 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2010/01/11 11:16
L10	131	9 and (insulated adj gate adj field adj effect adj transistor)	US-PGPUB; USPAT	OR	ON	2010/01/11 11:16
L11	80	((trench or hole or groove or opening or aperture or recess) and (insulated adj gate adj field adj effect adj transistor) and (dope or doping or doped or implant or implanting or implanted or implantation) and concentration).clm.	US-PGPUB; USPAT	OR	ON	2010/01/11 11:22
L12	73	11 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2010/01/11 11:22
S1	1	("6160288").PN.	US-PGPUB; USPAT	OR	OFF	2008/09/26 14:12
S2	20422	insulated near3 gate with transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 18:00
S3	3657	S2 and trench	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S4	2406	S3 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S5	435	S4 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S6	332	S5 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 18:05
S7	91	S6 and ((base or bottom) with trench with (dop\$3 or implant\$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 18:06
S8	8726	trench near5 transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02
S9	6573	S8 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02

S10	3963	S9 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02
S11	415	S10 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S12	141	S11 and ((base or bottom) with trench with (dop\$3 or implant\$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S13	20422	insulated near3 gate with transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S14	3657	S13 and trench	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S15	2406	S14 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S16	435	S15 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S17	332	S16 and @ad< "20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S18	91	S17 and ((base or bottom) with trench with (dop\$3 or implant\$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S19	114	S12 not S18	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S20	36	steven with t with peake	US-PGPUB; USPAT	OR	ON	2008/09/26 22:37
S21	32	S20 and @ad< "20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:37
S22	21	steven with t with peake	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/26 22:40
S23	2652	trench near3 (FET or MOSFET)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S24	1959	S23 and @ad< "20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S25	602	S24 and ((base or bottom) with trench with (dop\$3 or implant\$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S26	559	S25 not S18	US-PGPUB; USPAT	OR	ON	2008/09/26 22:43
S27	533	S26 not S19	US-PGPUB; USPAT	OR	ON	2008/09/26 22:43
S28	212	S27 and (low with (doping or impurity or density))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:44
S29	11132	vertical near3 transistor	US-PGPUB; USPAT	OR	ON	2008/09/27 16:49
S30	2	S29 and (trench with (moat near3 etch\$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:50
S31	6107	trench near3 transistor	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53
S32	8	S31 and (trench with (moat near3 etch\$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53
S33	6	S32 and @ad< "20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53
S34	42	(trench with (moat near3 etch\$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:55

S35	31	S34 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 16:55
S36	3313	438/173,192,197,206,207,212.ccls.	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S37	2434	S36 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S38	150	S37 and ((base or bottom) with trench with (dop\$3 or implant\$5))	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S39	0	dose with concention	US-PGPUB; USPAT	OR	ON	2009/03/20 15:23
S40	56572	dose with concentration	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S41	42223	S40 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S42	663	S41 and (low near3 (doped or doping))	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S43	246	S42 and trench	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S44	224	S43 and transistor	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S45	37	S44 and (insulated with transistor)	US-PGPUB; USPAT	OR	ON	2009/03/20 15:25
S46	1	("20070141783").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/20 15:58
S48	1638	trench adj (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:07
S49	1181	S48 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/29 22:08
S50	1002	S49 and (gate with trench)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:08
S52	188	S50 and (p near3 n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:09
S53	181	S52 and drain	US-PGPUB; USPAT	OR	ON	2009/03/29 22:11
S54	1	("20070141783").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/30 07:23
S55	0	steven adj t adj peake	US-PGPUB; USPAT	OR	ON	2009/03/30 07:28
S56	40	steven with t with peake	US-PGPUB; USPAT	OR	ON	2009/03/30 07:29
S57	33	S56 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:29
S58	21	steven with t with peake	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/30 07:32
S59	11310	trench near5 (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34
S60	8033	S59 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34
S61	1271	S60 and (p with n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34

S62	582	S61 and body and drain	US-PGPUB; USPAT	OR	ON	2009/03/30 07:35
S63	467	S62 and concentration	US-PGPUB; USPAT	OR	ON	2009/03/30 07:35
S64	1638	trench adj (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S65	1181	S64 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S66	1002	S65 and (gate with trench)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S67	188	S66 and (p near3 n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S68	181	S67 and drain	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S69	352	S63 not S68	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S71	7470	(insulated adj gate adj field adj effect adj transistor)	US-PGPUB; USPAT	OR	ON	2010/01/11 10:45
S72	6266	S71 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2010/01/11 10:45
S73	3540	S72 and (trench or groove or opening or hole or aperture or recess)	US-PGPUB; USPAT	OR	ON	2010/01/11 10:46
S74	992	S73 and ((doping or doped or dope or implant or implanting or implanted or implantation) with (trench or groove or opening or hole or aperture or recess))	US-PGPUB; USPAT	OR	ON	2010/01/11 10:47
S75	158	S74 and (p adj n adj junction)	US-PGPUB; USPAT	OR	ON	2010/01/11 10:48
S76	2171	(insulated adj gate adj field adj effect adj transistor)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 10:52
S81	63	steven with t with peake	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 10:55

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